Trench-based Dual Schottky Rectifier, Very Low Forward Voltage, 20A, 100V

Features

- Fine Lithography Trench-based Schottky Technology for Very Low Forward Voltage and Low Leakage
- Fast Switching with Exceptional Temperature Stability
- Low Power Loss and Lower Operating Temperature
- Higher Efficiency for Achieving Regulatory Compliance
- Low Thermal Resistance
- High Surge Capability
- These are Pb-Free Devices

Typical Applications

- Switching Power Supplies including Notebook / Netbook Adapters, ATX and Flat Panel Display
- High Frequency and DC-DC Converters
- Freewheeling and OR-ing diodes
- Reverse Battery Protection
- Instrumentation

Mechanical Characteristics

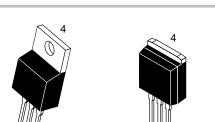
- Case: Epoxy, Molded
- Epoxy Meets Flammability Rating UL 94-0 @ 0.125 in
- Finish: All External Surfaces Corrosion Resistant and Terminal Leads are Readily Solderable
- Lead Temperature for Soldering Purposes: 260°C Maximum for 10 sec



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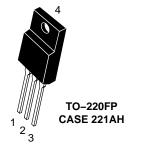
PIN CONNECTIONS



TO-220AB

CASE 221A

STYLE 6





I2PAK

CASE 418D

STYLE 3

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 5 of this data sheet.

MAXIMUM RATINGS

| Rating | | Symbol | Value | Unit |
|---|-------------------------|--|-------------|------|
| Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage | | V _{RRM} V _{RWM} V _R | 100 | V |
| Average Rectified Forward Current (Rated V _R , T _C = 130°C) | Per device Per diode | I _{F(AV)} | 20 10 | А |
| Peak Repetitive Forward Current (Rated V _R , Square Wave, 20 kHz, T _C = 125°C) | Per device Per diode | I _{FRM} | 40 20 | А |
| Nonrepetitive Peak Surge Current (Surge applied at rated load conditions halfwave, single phase, 60 Hz) | | I _{FSM} | 150 | А |
| Operating Junction Temperature | | TJ | -40 to +150 | °C |
| Storage Temperature | | T _{stg} | -40 to +150 | °C |
| Voltage Rate of Change (Rated V _R) | | dv/dt | 10,000 | V/µs |

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

THERMAL CHARACTERISTICS

| Rating | Symbol | NTST20100CTG, NTSB20100CT-1G | NTSB20100CTG | NTSJ20100CTG | Unit |
|---|-------------------------------|---------------------------------|--------------|--------------|------|
| Maximum Thermal Resistance per Diode Junction-to-Case Junction-to-Ambient | $R_{	heta JC} \ R_{	heta JA}$ | 2.5 70 | 1.5 46.9 | 4.49 105 | °C/W |

ELECTRICAL CHARACTERISTICS (Per Leg unless otherwise noted)

| Rating | Symbol | Тур | Max | Unit |
|---|----------------|--------------|-----------|----------|
| Maximum Instantaneous Forward Voltage (Note 1) | ٧ _F | 0.55 | | V |
| $(I_F = 5 A, T_J = 25^{\circ}C)$ $(I_F = 10 A, T_J = 25^{\circ}C)$ | | 0.55 0.65 | 0.83 | |
| (I _F = 5 A, T _J = 125°C) (I _F = 10 A, T _J = 125°C) | | 0.50 0.58 | - 0.68 | |
| Maximum Instantaneous Reverse Current (Note 1) $(V_R = 70 \text{ V}, T_J = 25^{\circ}\text{C})$ | I _R | 17 | _ | μΑ |
| $(V_R = 70 \text{ V}, T_J = 125^{\circ}\text{C})$ | | 5.3 | _ | mA |
| (Rated dc Voltage, T _J = 25°C) (Rated dc Voltage, T _J = 125°C) | | _ 12 | 800 25 | μA mA |

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

^{1.} Pulse Test: Pulse Width = 300 μ s, Duty Cycle $\leq 2.0\%$

TYPICAL CHARACTERISITICS

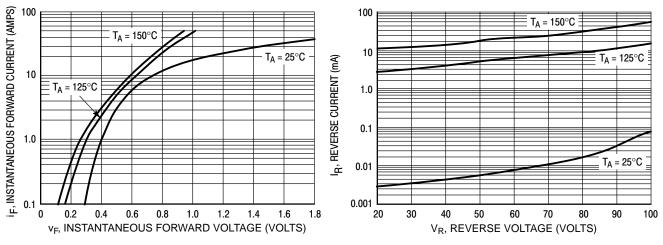


Figure 1. Typical Forward Voltage

Figure 2. Typical Reverse Current

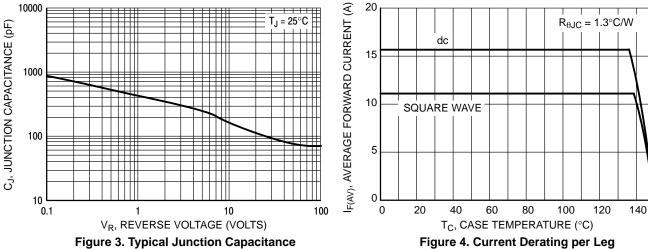


Figure 3. Typical Junction Capacitance

 $R_{\theta JC} = 1.3^{\circ}C/W$

40

35

30

25

20

15 10

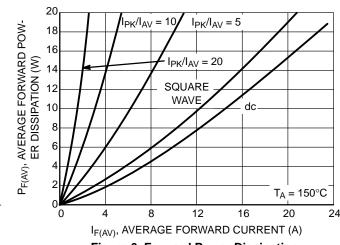
0

dc

SQUARE WAVE

20

I_{F(AV)}, AVERAGE FORWARD CURRENT (A)



T_C, CASE TEMPERATURE (°C) Figure 5. Current Derating

60

80

100

120

140

Figure 6. Forward Power Dissipation

TYPICAL CHARACTERISITICS

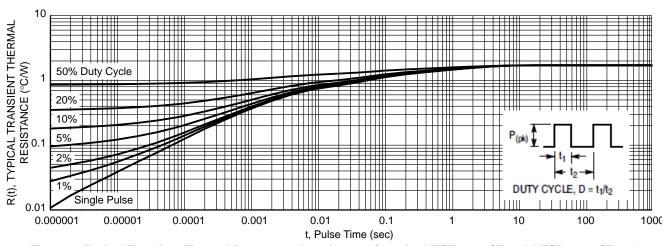


Figure 7. Typical Transient Thermal Response, Junction-to-Case for NTST20100CT and NTSB20100CT-1G

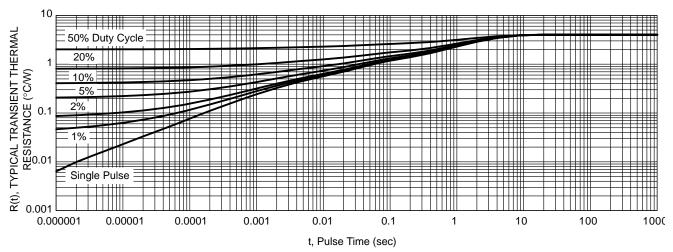


Figure 8. Typical Transient Thermal Response, Junction-to-Case for NTSJ20100CTG

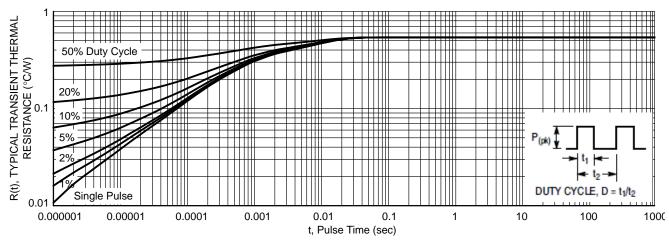
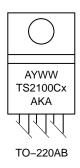


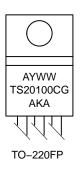
Figure 9. Typical Transient Thermal Response for NTSB20100CTG

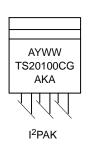
ORDERING INFORMATION

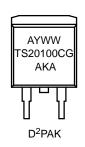
| Device | Package | Shipping |
|----------------|---------------------------------|-------------------|
| NTST20100CTG | TO-220AB (Pb-Free) | 50 Units / Rail |
| NTSB20100CT-1G | I ² PAK (Pb-Free) | 50 Units / Rail |
| NTSJ20100CTG | TO-220FP (Halide-Free) | 50 Units / Rail |
| NTSB20100CTG | D ² PAK (Pb-Free) | 50 Units / Rail |
| NTSB20100CTT4G | D ² PAK (Pb-Free) | 800 / Tape & Reel |

MARKING DIAGRAMS









A = Assembly Location

Y = Year WW = Work Week AKA = Polarity Designator

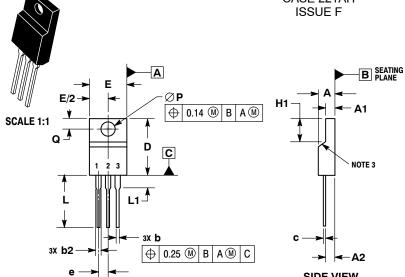
x = G or H

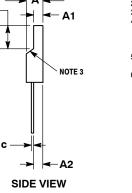
G = Pb-Free Package H = Halide-Free Package



ISSUE F

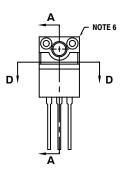
DATE 30 SEP 2014

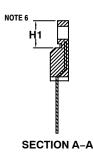






FRONT VIEW





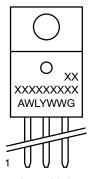
ALTERNATE CONSTRUCTION

NOTES:

- DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
- 2. CONTROLLING DIMENSION: MILLIMETERS.
 3. CONTOUR UNCONTROLLED IN THIS AREA.
- CONTOUR ONCOUNT HOLLED IN THIS AREA.
 DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH AND GATE PROTRUSIONS. MOLD FLASH AND GATE PROTRUSIONS NOT TO EXCEED 0.13 PER SIDE. THESE DIMENSIONS ARE TO BE MEASURED AT OUTERMOST EXTREME OF THE PLASTIC BODY.
 DIMENSION b2 DOES NOT INCLUDE DAMBAR PROTRUSION.
 LEAD WIDTH INCLUDING PROTRUSION SHALL NOT EXCEED 2.00.
- CONTOURS AND FEATURES OF THE MOLDED PACKAGE BODY MAY VARY WITHIN THE ENVELOP DEFINED BY DIMENSIONS AT AND H1 FOR MANUFACTURING PURPOSES.

| | THE THE COLUMN TO COLUMN | | | | |
|-----|--------------------------|-------|--|--|--|
| | MILLIMETERS | | | | |
| DIM | MIN | MAX | | | |
| Α | 4.30 | 4.70 | | | |
| A1 | 2.50 | 2.90 | | | |
| A2 | 2.50 | 2.90 | | | |
| b | 0.54 | 0.84 | | | |
| b2 | 1.10 | 1.40 | | | |
| С | 0.49 | 0.79 | | | |
| D | 14.70 | 15.30 | | | |
| E | 9.70 | 10.30 | | | |
| е | 2.54 | BSC | | | |
| H1 | 6.60 | 7.10 | | | |
| L | 12.50 | 14.73 | | | |
| L1 | | 2.80 | | | |
| P | 3.00 | 3.40 | | | |
| Q | 2.80 | 3.20 | | | |

GENERIC MARKING DIAGRAM*



= Assembly Location

WL = Wafer Lot

= Year

WW = Work Week

G = Pb-Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot " ■", may or may not be present.

| STYLE 1: | | STYLE 2: | |
|----------|-----------------|----------|---------|
| PIN 1. | MAIN TERMINAL 1 | PIN 1. | CATHODE |
| 2. | MAIN TERMINAL 2 | 2. | ANODE |
| 3. | GATE | 3. | GATE |

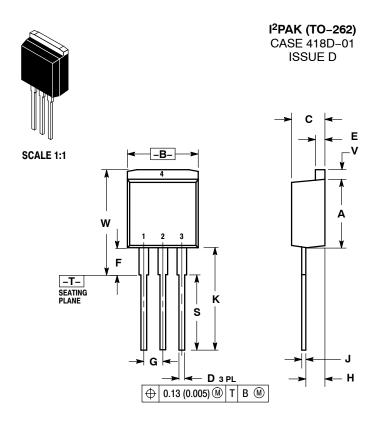
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| DESCRIPTION: | TO-220 FULLPACK, 3-LEA | AD | PAGE 1 OF 1 |

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MECHANICAL CASE OUTLINE PACKAGE DIMENSIONS

ON Semiconductor®





DATE 16 OCT 2007

NOTES:

- DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
- 2. CONTROLLING DIMENSION: INCH.

| | INCHES | | MILLIN | IETERS |
|-----|-----------|-------|----------|--------|
| DIM | MIN | MAX | MIN | MAX |
| Α | 0.335 | 0.380 | 8.51 | 9.65 |
| В | 0.380 | 0.406 | 9.65 | 10.31 |
| С | 0.160 | 0.185 | 4.06 | 4.70 |
| D | 0.026 | 0.035 | 0.66 | 0.89 |
| Е | 0.045 | 0.055 | 1.14 | 1.40 |
| F | 0.122 REF | | 3.10 REF | |
| G | 0.100 | BSC | 2.54 | BSC |
| Н | 0.094 | 0.110 | 2.39 | 2.79 |
| J | 0.013 | 0.025 | 0.33 | 0.64 |
| K | 0.500 | 0.562 | 12.70 | 14.27 |
| S | 0.390 REF | | 9.90 | REF |
| ٧ | 0.045 | 0.070 | 1.14 | 1.78 |
| W | 0.522 | 0.551 | 13.25 | 14.00 |

| STYLE 1: | STYLE 2: | STYLE 3: | STYLE 4: |
|-----------------------------|--------------------------|--------------|-------------------------------|
| PIN 1. BASE | PIN 1. GATE | PIN 1. ANODE | PIN 1. GATE |
| 2. COLLECTOR | 2. DRAIN | 2. CATHODE | 2. COLLECTOR |
| EMITTER | SOURCE | 3. ANODE | 3. EMITTER |
| COLLECTOR | 4. DRAIN | 4. CATHODE | COLLECTOR |

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| DESCRIPTION: | I ² PAK (TO-262) | | PAGE 1 OF 1 |

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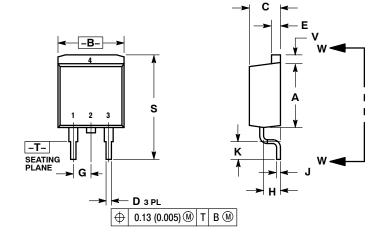




D²PAK 3 CASE 418B-04 **ISSUE L**

DATE 17 FEB 2015

SCALE 1:1



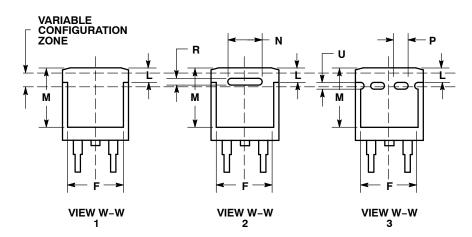
- DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
 CONTROLLING DIMENSION: INCH.
- 3. 418B-01 THRU 418B-03 OBSOLETE,

NEW STANDARD 418B-04.

| INCHES | | MILLIMETERS | |
|-----------|--|---|---|
| MIN | MAX | MIN | MAX |
| 0.340 | 0.380 | 8.64 | 9.65 |
| 0.380 | 0.405 | 9.65 | 10.29 |
| 0.160 | 0.190 | 4.06 | 4.83 |
| 0.020 | 0.035 | 0.51 | 0.89 |
| 0.045 | 0.055 | 1.14 | 1.40 |
| 0.310 | 0.350 | 7.87 | 8.89 |
| 0.100 BSC | | 2.54 BSC | |
| 0.080 | 0.110 | 2.03 | 2.79 |
| 0.018 | 0.025 | 0.46 | 0.64 |
| 0.090 | 0.110 | 2.29 | 2.79 |
| 0.052 | 0.072 | 1.32 | 1.83 |
| 0.280 | 0.320 | 7.11 | 8.13 |
| 0.197 REF | | 5.00 | REF |
| 0.079 | REF | 2.00 | REF |
| 0.039 | REF | 0.99 | REF |
| | MIN 0.340 0.380 0.160 0.020 0.045 0.310 0.100 0.080 0.018 0.090 0.052 0.280 0.197 | MIN MAX 0.340 0.380 0.380 0.405 0.180 0.190 0.020 0.035 0.045 0.055 0.310 0.350 0.100 BSC 0.080 0.110 0.018 0.025 0.090 0.110 0.052 0.072 0.280 0.320 | MIN MAX MIN 0.340 0.380 8.64 0.380 0.405 9.65 0.160 0.190 4.06 0.020 0.035 0.51 0.045 0.055 1.14 0.310 0.350 7.87 0.100 BSC 2.54 0.080 0.110 2.03 0.018 0.025 0.46 0.090 0.110 2.29 0.052 0.072 1.32 0.280 0.320 7.11 0.197 REF 5.00 0.079 REF 2.00 |

 S
 0.575
 0.625
 14.60
 15.88

 V
 0.045
 0.055
 1.14
 1.40



STYLE 1: PIN 1. BASE 2. COLLECTOR
3. EMITTER
4. COLLECTOR STYLE 2: PIN 1. GATE 2. DRAIN 3. SOURCE 4. DRAIN STYLE 3: PIN 1. ANODE 2. CATHODE 3. ANODE 4. CATHODE

STYLE 4:

PIN 1. GATE 2. COLLECTOR 3. EMITTER 4. COLLECTOR STYLE 5: PIN 1. CATHODE 2. ANODE 3. CATHODE 4. ANODE

STYLE 6: PIN 1. NO CONNECT 2. CATHODE 3. ANODE 4. CATHODE

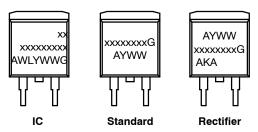
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DATE 17 FEB 2015

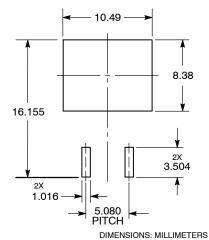
GENERIC MARKING DIAGRAM*



xx = Specific Device Code A = Assembly Location

WL = Wafer Lot
Y = Year
WW = Work Week
G = Pb-Free Package
AKA = Polarity Indicator

SOLDERING FOOTPRINT*



*For additional information on our Pb-Free strategy and soldering details, please download the **onsemi** Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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